Silicon PNP Epitaxial, Darlington

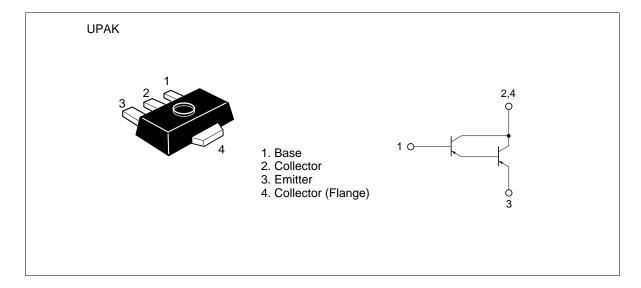
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ADE-208-1040 (Z) 1st. Edition Mar. 2001

Application

High gain amplifier

Outline





Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-60	V
Collector to emitter voltage	V _{CEO}	-60	V
Emitter to base voltage	V _{EBO}	-7	V
Collector current	Ι _c	-1	А
Collector peak current	i _{C(peak)} *1	-2	А
Collector power dissipation	P _c * ²	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \text{ ms}$, Duty cycle $\le 20\%$

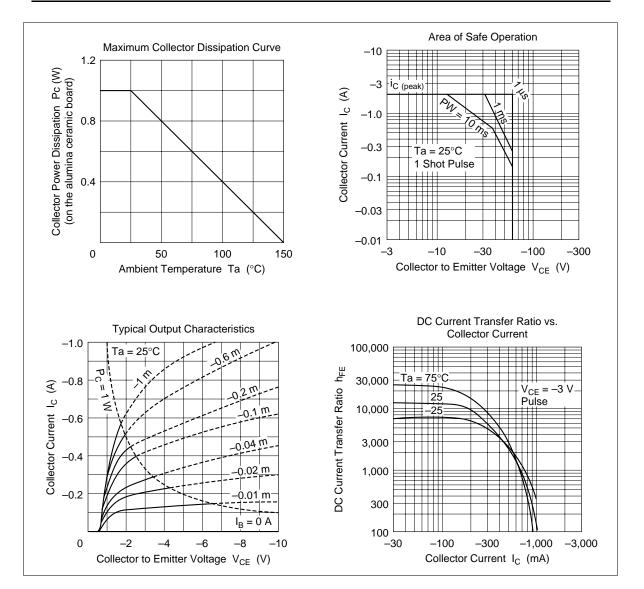
2. Value on the alumina ceramic board (12.5 \times 30 \times 0.7 mm)

Electrical Characteristics (Ta = 25°C)

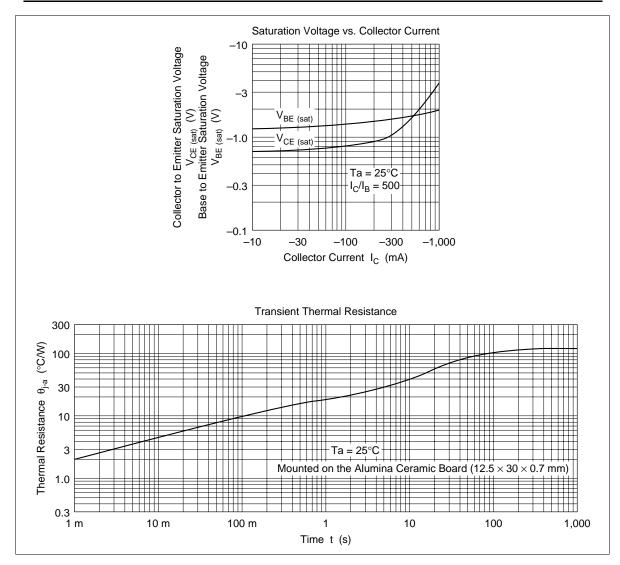
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	-60	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	-60	_	_	V	$I_c = -1 \text{ mA}, \text{ R}_{BE} = \infty$
Collector cutoff current	I _{CBO}	—	—	-10	μA	$V_{CB} = -60 \text{ V}, \text{ I}_{E} = 0$
Emitter cutoff current	I _{EBO}	—	—	-10	μA	$V_{EB} = -7 V, I_{E} = 0$
DC current transfer ratio	h _{FE}	2000	—	100000)	$V_{ce} = -3 \text{ V}, \text{ I}_{c} = -500 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-2.0	V	$I_{c} = -500 \text{ mA}, I_{B} = -1 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	—	_	-2.0	V	$I_{c} = -500 \text{ mA}, I_{B} = -1 \text{ mA}^{*1}$

Notes: 1. Pulse test

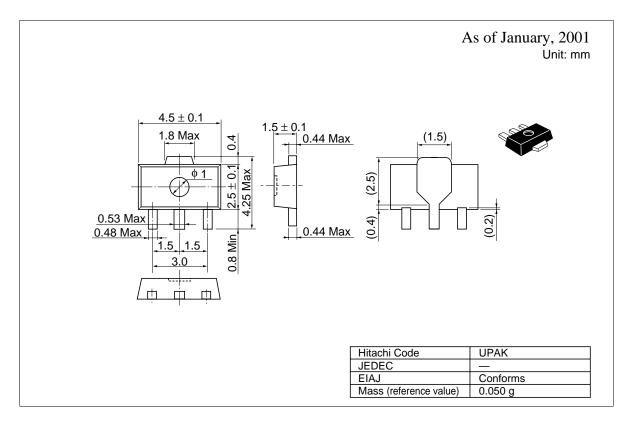
2. Marking is "BT"



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Package Dimensions



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